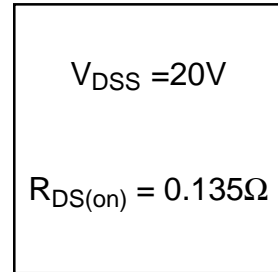
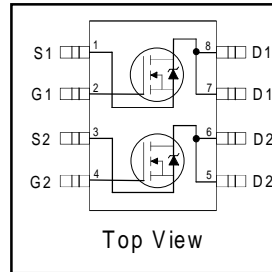


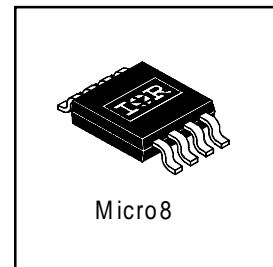
- Generation V Technology
- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Very Small SOIC Package
- Low Profile (<1.1mm)
- Available in Tape & Reel
- Fast Switching



Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The new Micro8 package, with half the footprint area of the standard SO-8, provides the smallest footprint available in an SOIC outline. This makes the Micro8 an ideal device for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro8 will allow it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards.



Absolute Maximum Ratings

	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	20	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	2.4	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	1.9	
I _{DM}	Pulsed Drain Current ①	19	
P _D @ T _A = 25°C	Maximum Power Dissipation④	1.25	W
P _D @ T _A = 70°C	Maximum Power Dissipation ④	0.8	W
	Linear Derating Factor	0.01	W/°C
V _{GSM}	Gate-to-Source Voltage Single Pulse tp<10μs	16	V
V _{GS}	Gate-to-Source Voltage	± 12	V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	V/ns
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	240 (1.6mm from case)	

Thermal Resistance

	Parameter	Max.	Units
R _{θJA}	Maximum Junction-to-Ambient ④	100	°C/W

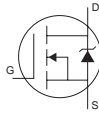
All Micro8 Data Sheets reflect improved Thermal Resistance, Power and Current -Handling Ratings- effective only for product marked with Date Code 505 or later .

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	20	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.041	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	0.085	0.135	Ω	V _{GS} = 4.5V, I _D = 1.7A ④
		—	0.120	0.20		V _{GS} = 2.7V, I _D = 0.85A ④
V _{GS(th)}	Gate Threshold Voltage	0.70	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	2.6	—	—	S	V _{DS} = 10V, I _D = 0.85A
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 16V, V _{GS} = 0V
		—	—	25		V _{DS} = 16V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -12V
Q _g	Total Gate Charge	—	5.3	8.0	nC	I _D = 1.7A
Q _{gs}	Gate-to-Source Charge	—	0.84	1.3		V _{DS} = 16V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	2.2	3.3		V _{GS} = 4.5V, See Fig. 9 ④
t _{d(on)}	Turn-On Delay Time	—	5.7	—	ns	V _{DD} = 10V
t _r	Rise Time	—	24	—		I _D = 1.7A
t _{d(off)}	Turn-Off Delay Time	—	15	—		R _G = 6.0Ω
t _f	Fall Time	—	16	—		R _D = 5.7Ω ④
C _{iss}	Input Capacitance	—	260	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	130	—		V _{DS} = 15V
C _{rss}	Reverse Transfer Capacitance	—	61	—		f = 1.0MHz, See Fig. 8

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	1.25	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	19		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 1.7A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	39	59	ns	T _J = 25°C, I _F = 1.7A
Q _{rr}	Reverse Recovery Charge	—	37	56	nC	di/dt = 100A/μs ③

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 10)

② I_{SD} ≤ 1.7A, di/dt ≤ 66A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C

③ Pulse width ≤ 300μs; duty cycle ≤ 2%

④ Surface mounted on FR-4 board, t ≤ 10sec

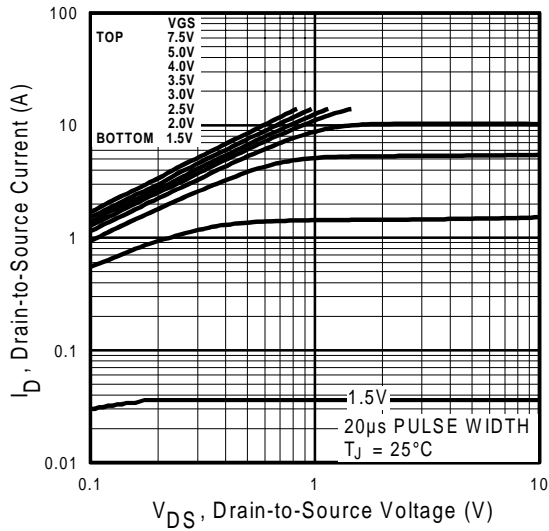


Fig 1. Typical Output Characteristics

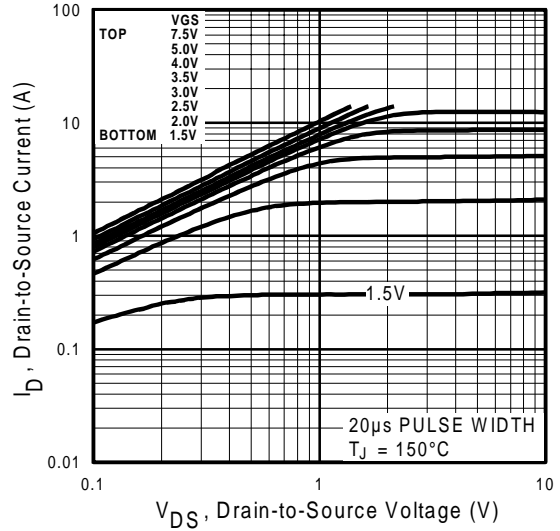


Fig 2. Typical Output Characteristics

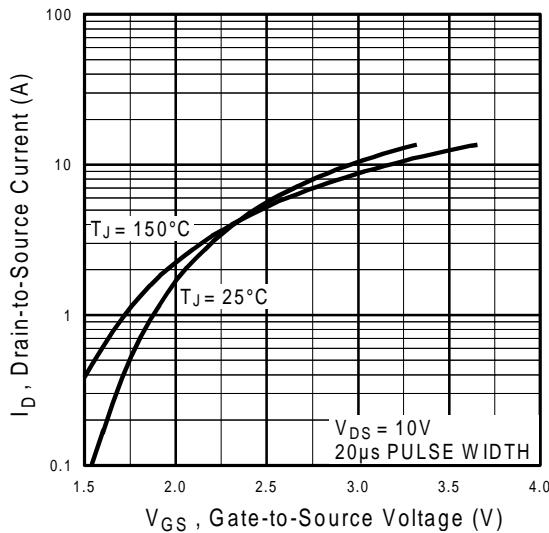


Fig 3. Typical Transfer Characteristics

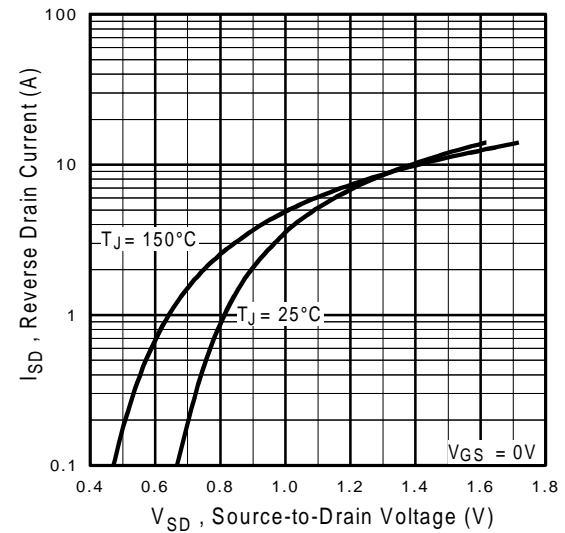


Fig 7. Typical Source-Drain Diode Forward Voltage

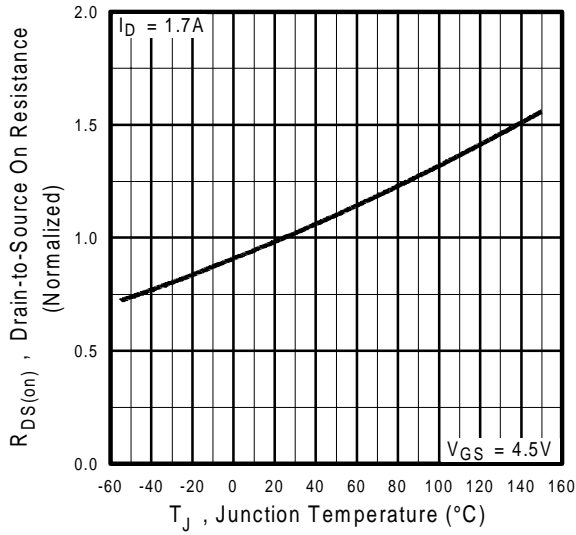


Fig 5. Normalized On-Resistance Vs. Temperature

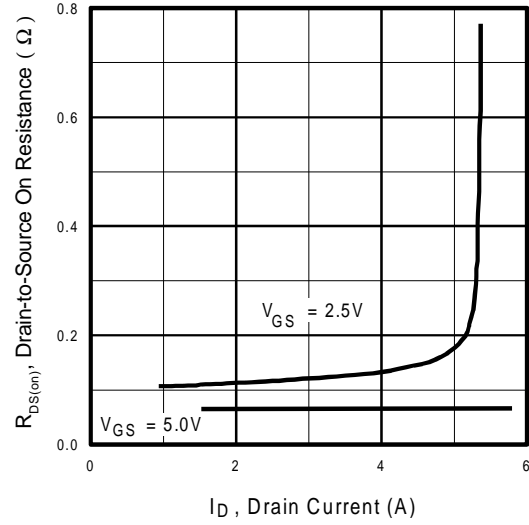


Fig 6. Typical On-Resistance Vs. Drain Current

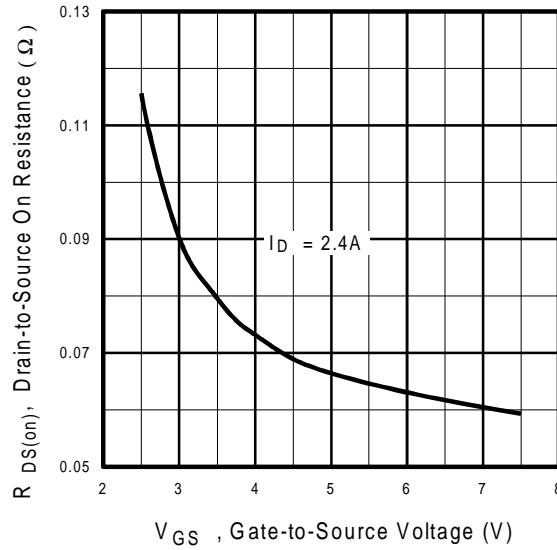


Fig 7. Typical On-Resistance Vs. Gate Voltage

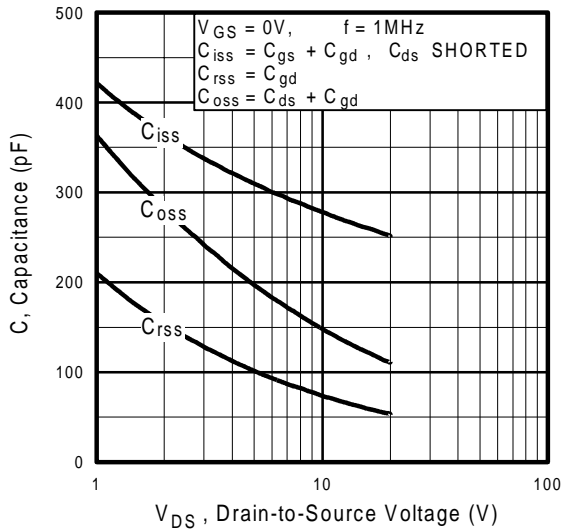


Fig 8. Typical Capacitance Vs. Drain-to-Source Voltage

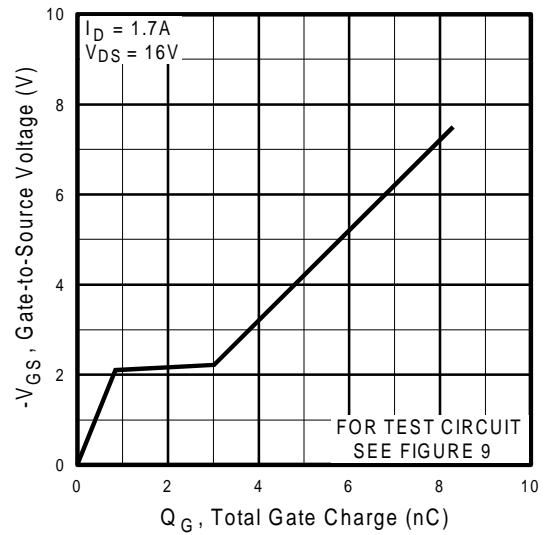


Fig 9. Typical Gate Charge Vs. Gate-to-Source Voltage

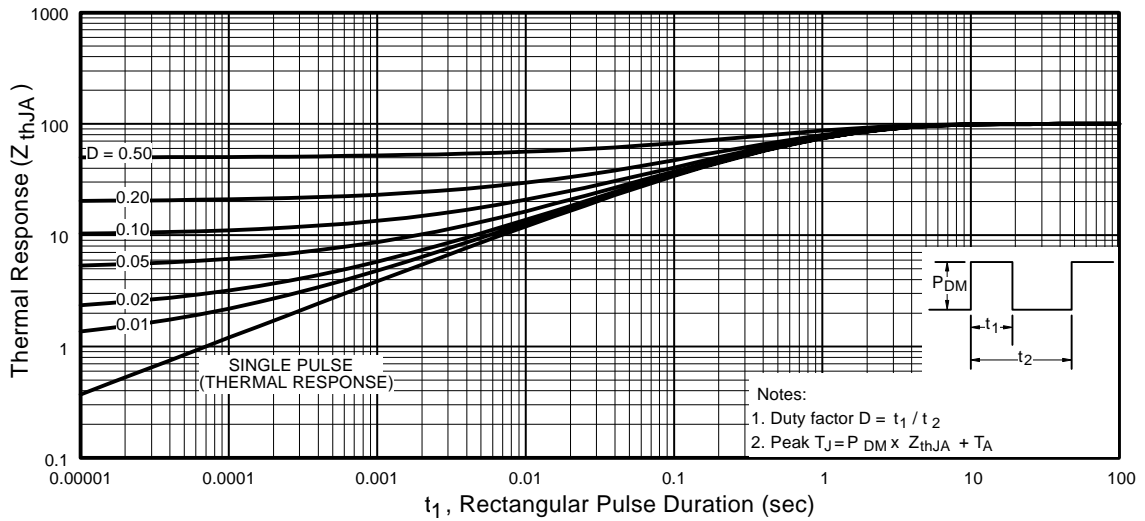
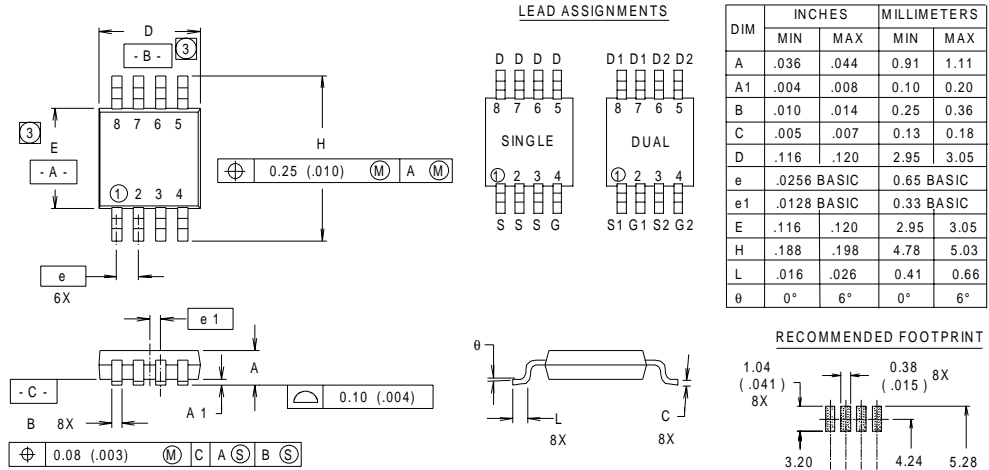


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRF7501



Micro8 Package Outline

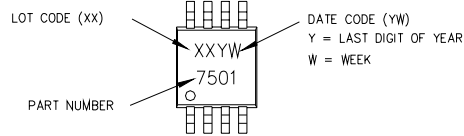


NOTES:
 1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
 2 CONTROLLING DIMENSION : INCH.
 3 DIMENSIONS DO NOT INCLUDE MOLD FLASH.

Part Marking Information

IRF7501 example

EXAMPLE: THIS IS AN IRF7501



WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

DATE CODE EXAMPLES:
 YW = 9503 = 5C
 YW = 9532 = EF

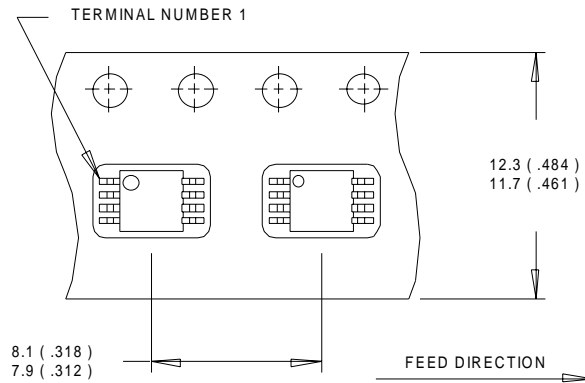
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2002	2	02	B
2003	3	03	C
1994	4	04	D
1995	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

WW = (27-52) IF PRECEDED BY A LETTER

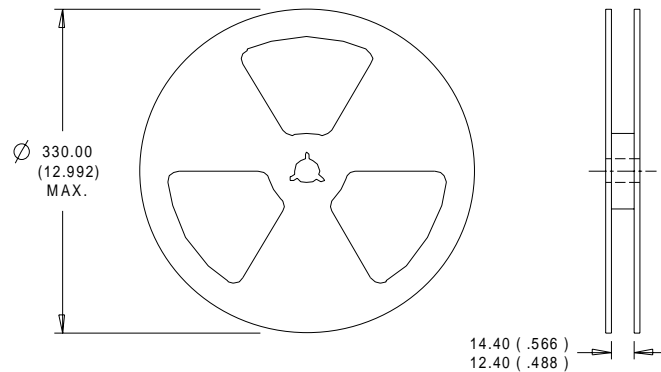
YEAR	Y	WORK WEEK	W
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2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

Tape & Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. OUTLINE CONFORMS TO EIA-481 & EIA-541.
 2. CONTROLLING DIMENSION : MILLIMETER.



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